



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Fabrice LETERTRE Confirmation No.: 6657
Application No.: 10/716,451 Group Art Unit: 1765
Filing Date: November 20, 2003 Examiner:
For: METHOD OF FABRICATING Attorney Docket No.: 4717-11500
MONOCRYSTALLINE CRYSTALS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed is a Form PTO-1449 listing eleven (11) references for the Examiner's review. The references were cited in the Search Report for the corresponding French application, and a copy of the Search Report is enclosed.

Copies of non-U.S. patent references B1-B6 and C1-C5 are enclosed herewith. Copies of U.S. patent references A1-A3 will be provided if the Examiner so requests.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

This Information Disclosure Statement is filed under § 37 CFR 1.97(b)(3), before the mailing of a first Office Action on the merits. Thus, no fee is believed to be due. Should a fee be required, however, please charge such fee to Winston & Strawn LLP Deposit Account No. 50-1814.

Respectfully submitted,

April 26, 2004
Date

E. Bradley Gould (Reg. No. 41,792)
For: Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN LLP
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202-371-5904

LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i>				ATTY. DOCKET NO.: 4717-11500		APPLICATION NO.: 10/716,451	
				APPLICANT: Fabrice LETERTRE			
				FILING DATE: November 20, 2003		GROUP: 1765	
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A1	6,328,796 B1	12/2001	Kub et al.	117	94	
	A2	2002/0096106	07/2002	Kub et al.	117	94	
	A3	2003/0036247	02/2003	Eriksen et al.	438	455	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	B1	WO 96/41906	12/1996	PCT			
	B2	EP 0 961 312	01/1999	EPO			
	B3	WO 01/68957	09/2001	PCT			
	B4	JP 2001 253799	09/2001	Japan (with English abstract)			X
	B5	EP 1 245 702	02/2002	EPO			
	B6	JP 2003 183097	07/2003	Japan (with English abstract)			X
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)							
	C1	Hugonnard-Bruyère, E., et al., "Deep Level Defectss in H ⁺ Implanted 6H-SiC Epilayers and in Silicon Carbide on Insulator Structures", <i>Materials Science and Engineering B</i> , Vol. 61-62, pp. 382-388 (1999)					
	C2	Hugonnard-Bruyère, E., et al., "Defect Studies in Epitaxial SiC-6H Layers on Insulator (SiCOI)", <i>Microelectronic Engineering</i> , Vol. 48, pp. 277-280 (1999)					
	C3	Müller, S.G, et al., "Progress in the Industrial Production of SiC Substrates for Semiconductor Devices", <i>Materials and Science Engineering B</i> , Vol. 80, No. 1-3, pp. 327-331 (2001)					
	C4	Tsvetkov, V. et al., "SiC Seeded Boule Growth", <i>Materials Science Forum</i> , Vols. 264-268, pp. 3-8 (1998)					
	C5	Tsvetkov, V.F. et al., "Recent Progress in SiC Crystal Growth", <i>Inst. Phys. Conf. Ser.</i> , No. 142, Chap. 1, pp. 17-22 (1996)					
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							